

# Magnetic oxide $\text{Fe}_{2-x}\text{Ti}_x\text{O}_{3-\delta}$ as a spintronics material



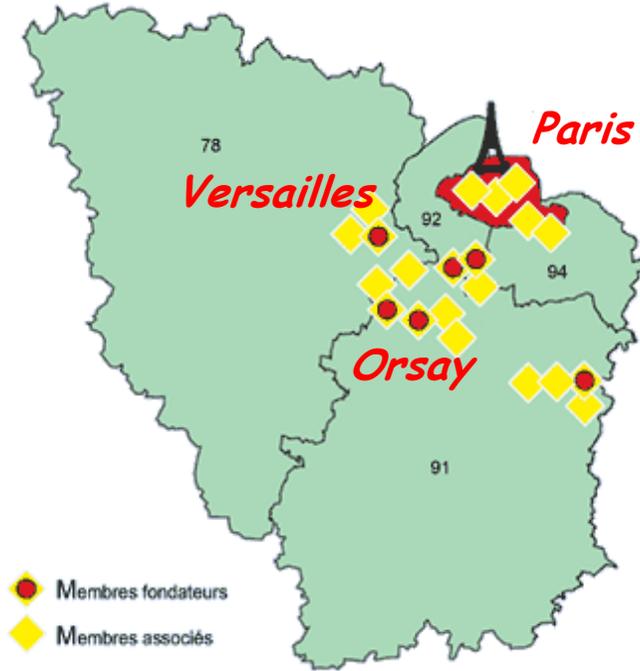
Yves Dumont

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Université de Versailles Saint Quentin en Yvelines - CNRS,  
France

# Versailles University (UVSQ):

[www.uvsq.fr](http://www.uvsq.fr)

Member of the new Large Scale Campus "Paris-Saclay University":



19 000 students  
160 academic programs  
35 laboratories  
1 360 professors and researchers  
700 doctoral students

A plural disciplinary University:

4 Schools of Humanities & Social Sciences, of Exact Sciences, of Law and Political Sciences, of Medicine

1 Engineering School

2 University technical Institutes

1 Universe Sciences Institute

International students = 9.2% of all enrolled students and 35.4% of doctoral students.

Close to a "more" famous castle ...



# Collaboration with TSU

## General bilateral exchange agreement between TSU - UVSQ (2009-2014)

- Initiated by Physics, but general frame of exchange of teachers, researchers, and students
- Others expertises of UVSQ : environment, sustainable development, chemistry, computing (agreement between GTU and UVSQ)

**In 2012 with support of CAMPUS FRANCE: first exchange of a french speaking master student Nino Ponjavidze from TSU**

### Continuous research collaboration with:

- Dr. Tamar Tchelidze on Semiconducting properties calculations
  - Pr. Alexander Shengelaya on EPR, FMR properties
- ⇒ Applications to SRNRF and french CNRS research project programs ...
- ⇒ European projects between Georgia, Germany, France, etc...



UNIVERSITE DE VERSAILLES  
SAINT-QUENTIN-EN-YVELINES



INTERNATIONAL MOBILITY AGREEMENT

BETWEEN

THE UNIVERSITY OF VERSAILLES SAINT-QUENTIN-EN-YVELINES

FACULTY OF SCIENCE  
(Versailles, France)

AND

IVANE JAVAKHISHVILI STATE UNIVERSITY OF TBILISI

FACULTY OF EXACT AND NATURAL SCIENCES  
(Tbilisi, Georgia)

# GEMAC-Versailles : GEMaC Lab = Condensed Matter Studies Laboratory

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- belongs to Versailles University and CNRS
- ~40 permanents; ~ 15 post-doc + PhD students
- director: Dr. Niels KELLER
- 5 research groups :
  - "Diamond for high temperature electronics"
  - "Photo commutable Molecular Solids"
  - " Nano-scale optics" : Near Field optics, single photon physics
  - " New semiconductors and properties": ZnO 2D, 1D; doping ; MOCVD
  - **"Functional complex oxides": magnetic, metal/insulator, SC oxides ; PLD**
- Facilities :
  - XRD, AFM, MFM, SIMS
  - Spectrophotometry, ellipsometry, Photo-L, cathodo-L, FTIR,  $\mu$ -Raman
  - Magnetometry : SQUID 5.5Tesla 2-400K ; VSM 9Tesla 2K-1000K
  - Electrical transport high impedance (resistivity, Hall)

# $\text{Fe}_{2-x}\text{Ti}_x\text{O}_{3-\delta}$ as a spintronics material

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## Context:

- Research on new functional oxides for spintronics injector
- Alternative approach to the “Diluted Magnetic Semiconductors” (DMS) way

## Goal:

- Inducing “carriers” in a High  $T_{\text{Curie}}$  ferrimagnetic oxide by cation substitution and oxygen off-stoichiometry
- Getting a spin polarization of carriers

## Tools:

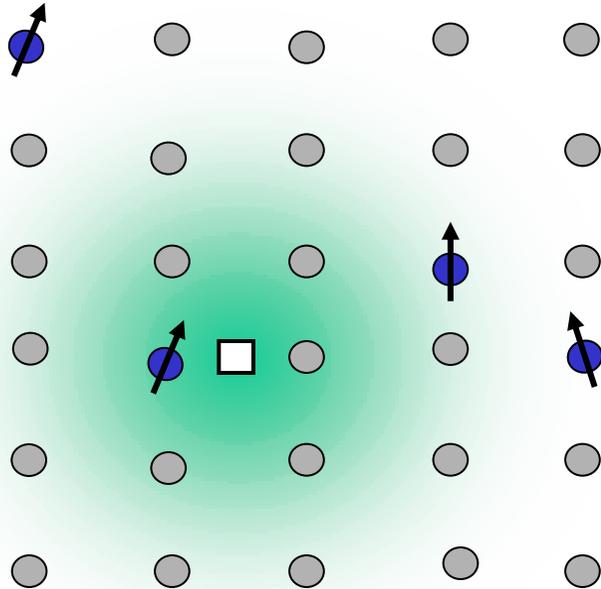
- Epitaxial films of  $\text{Fe}_{2-x}\text{Ti}_x\text{O}_{3-\delta}$  solid solution
- “MBE-type” Pulsed Laser Deposition (PLD) technique

## Questions:

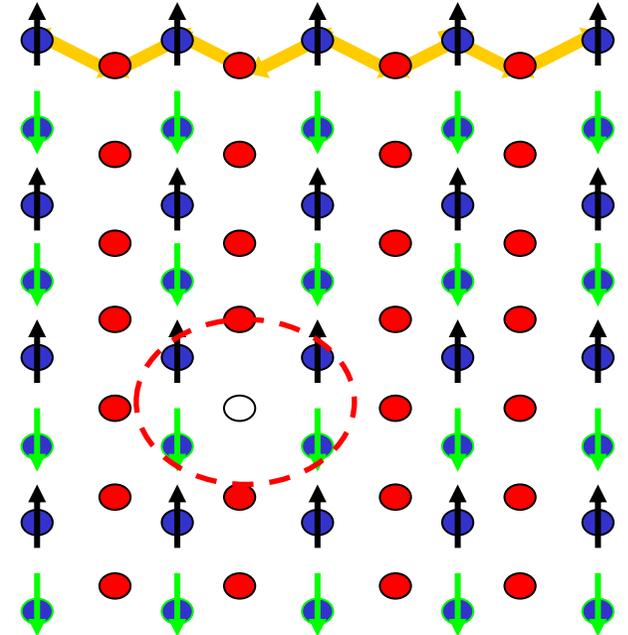
- Modification of the Fe-Fe interaction: super-exchange vs. double-exchange ?
- Conduction mechanisms: band vs. hopping ?
- Spin polarization ?

# Alternative approach to “DMS”

Diluted magnetic semiconductors



High  $T_C$  ( $> 400\text{K}$ )  
ferrimagnetic oxides



**Keeping the Semiconducting properties**  
**Getting a RT Ferromagnetism ...**

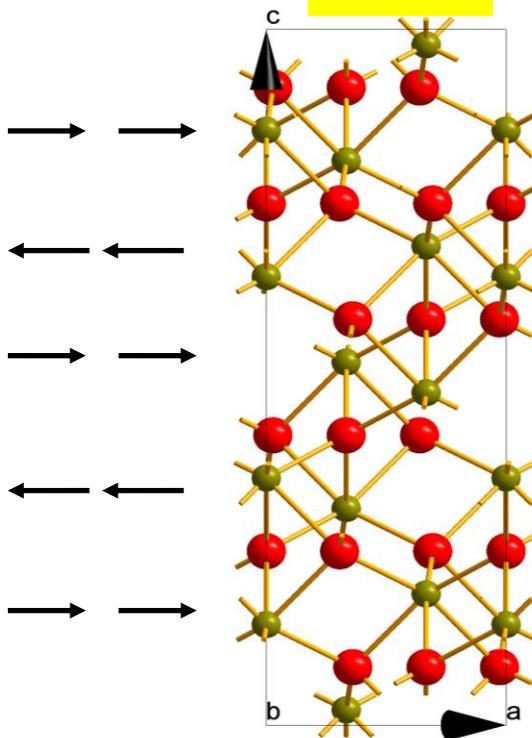


**Keeping the RT Ferrimagnetism**  
**Getting conductivity ...**

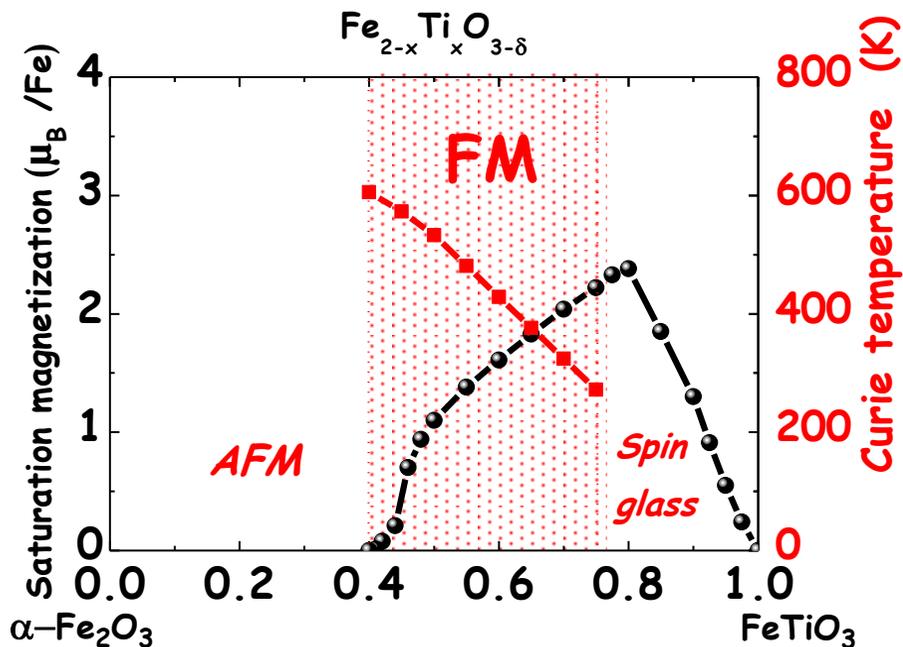


# System: $Fe_{2-x}Ti_xO_3$

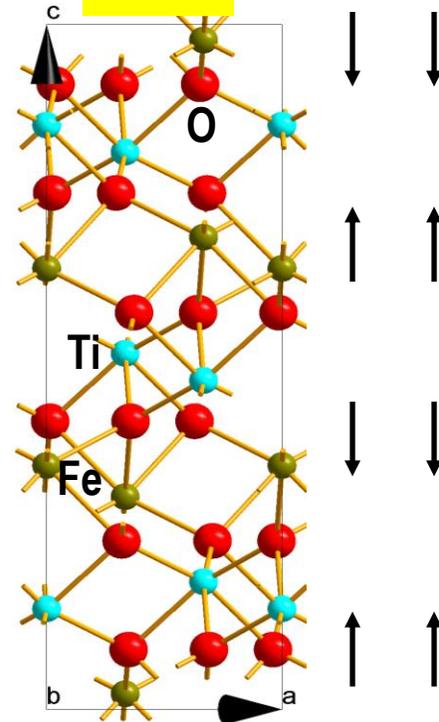
**R-3c**



*From polycrystalline bulk studies*



**R-3**



**Hematite**  
 **$\alpha-Fe_2O_3$ :**

Insulator ( $E_g=2.2$  eV)

Canted antiferromagnet: ( $T_c = 950K$   $T_{R,N} = 260K$ )

$260K < T < 950K$ ,  $M_S = 0.002 \mu_B$

*Y. Ishikawa and S. Akimoto, Jpn. J. Phys. Soc. 12, 1083 (1957), Y. Ishikawa, ibid. item 13, 37 (1958), 17, 12 (1962)*

**Ilmenite**  
 **$FeTiO_3$ :**

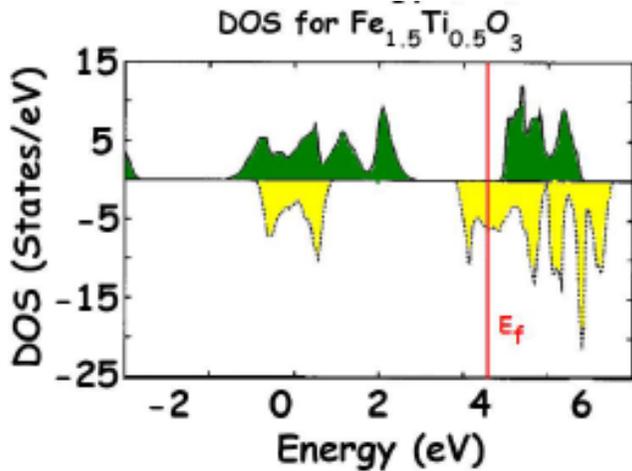
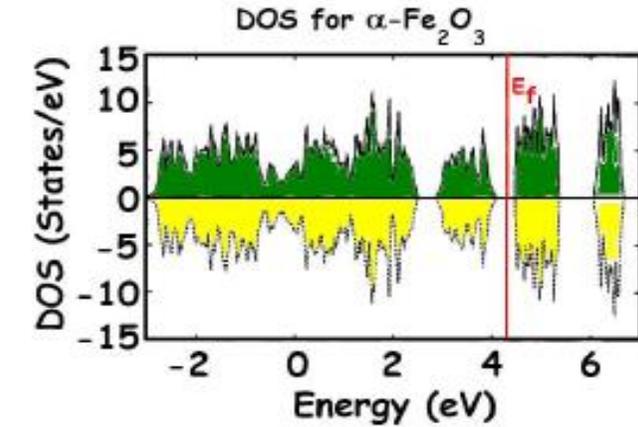
Insulator ( $E_g=3.3-3.6$  eV)

Antiferromagnet ( $T_N = 55K$ )

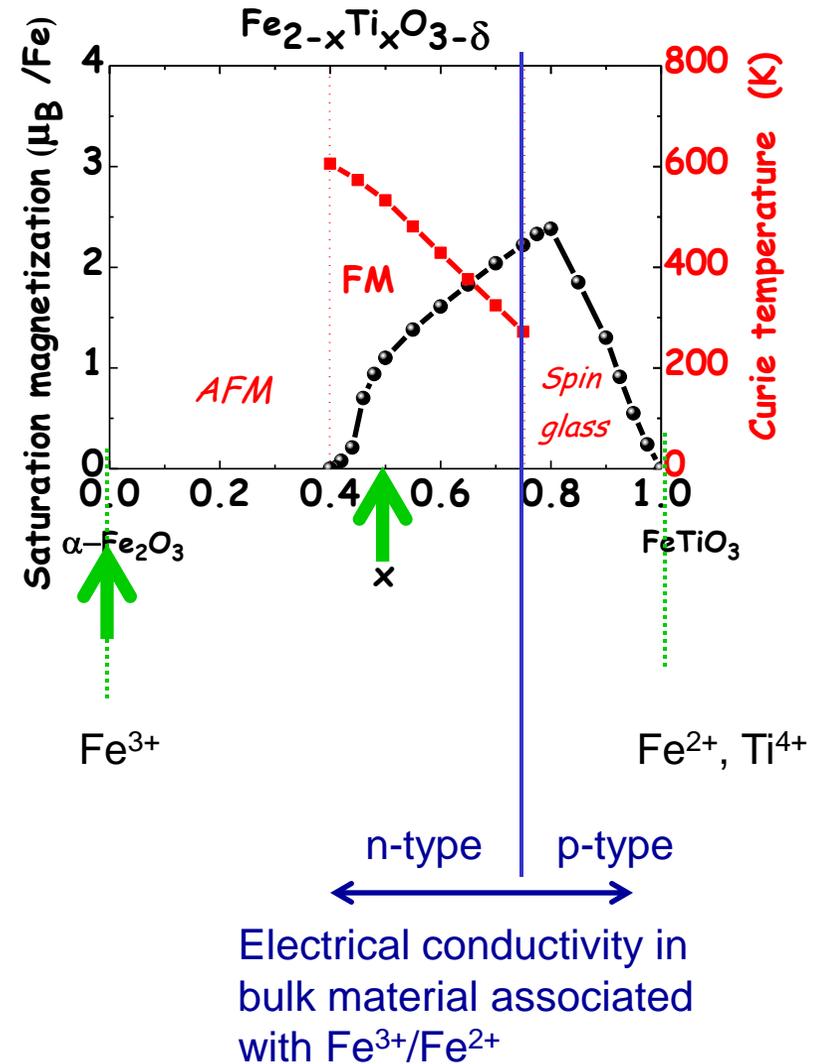
Non-equivalence of Fe et Ti sites

# System: $\text{Fe}_{2-x}\text{Ti}_x\text{O}_3$

*ab-initio calculations:*



*Predicted spin polarization for  $x=0.5$*



W. H. Butler et al., *J. Appl. Phys.* 93 (10), 7882 (2003)

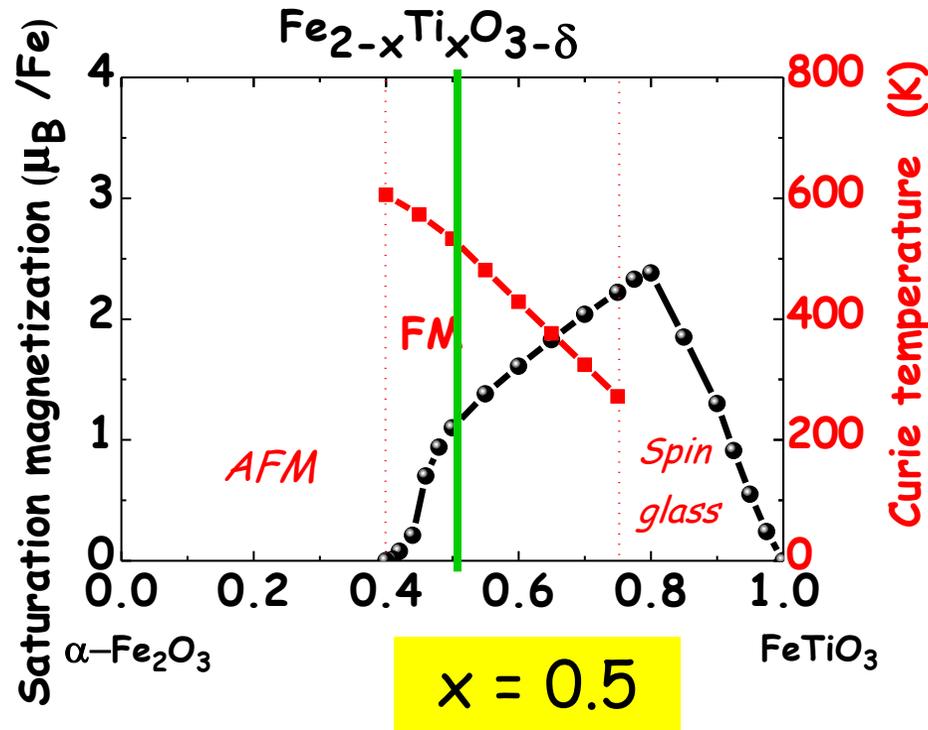
A. Bandyopadhyay et al., *Phys. Rev. B* 69, 174429 (2004)

# Studied compositions $Fe_{2-x}Ti_xO_{3-\delta}$

By a "MBE like"  
Pulsed Laser  
Deposition set-up:  
(base pressure :  
 $5 \times 10^{-9}$  torr,  
RHEED,  
spectroscopic  
ellipsometry)

$T_{\text{substrate}}$ : between  
650 and 750°C

$P_{O_2}$ : between  $10^{-7}$   
and  $10^{-1}$  torr



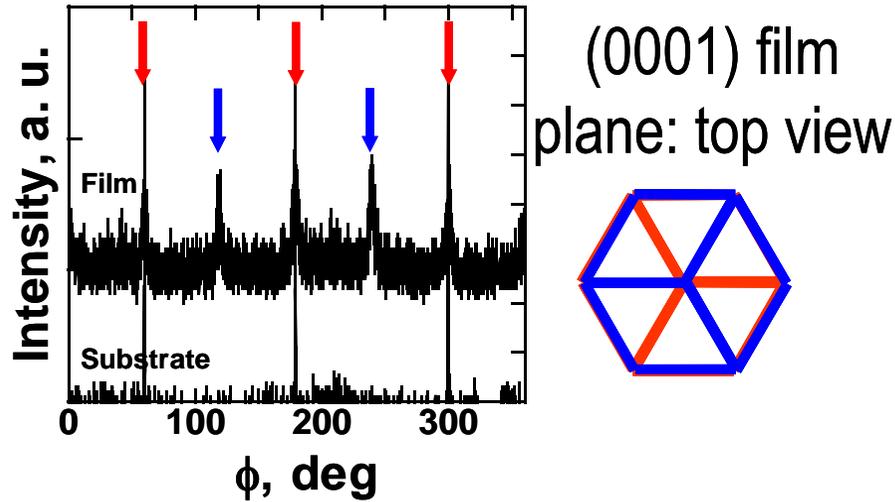
=> Epitaxy on iso-structural  $Al_2O_3(0001)$  and on cubic  $SrTiO_3(001)$

=> Tuning the oxygen off-stoichiometry  $\delta$

Thicknesses from 30 to 200 nm

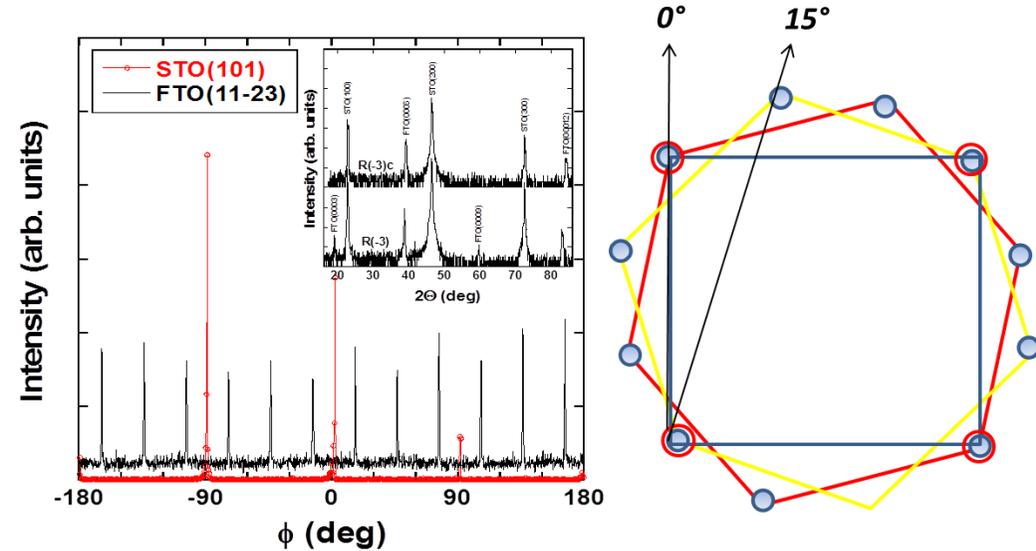
# Epitaxial growth on $\text{Al}_2\text{O}_3$ (0001) and $\text{SrTiO}_3$ (001)

on iso-structural  $\text{Al}_2\text{O}_3$  (0001)



*E. Popova et al., J. Appl. Phys. 103 (2008) 093909*  
*E. Popova et al., Surface Science 605 (2011) 1043*

on cubic (Si-compatible)  $\text{SrTiO}_3$  (001)



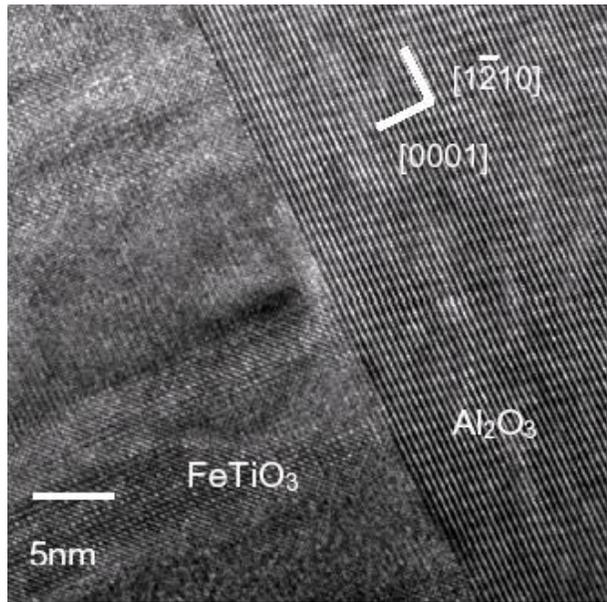
*A. Hamie et al., J. Appl. Phys. 108 (2010) 093710*  
*A. Hamie et al., Appl. Phys. Lett. 98 (2011) 232501*

R-3c phase mostly and special route for R-3  
 Epitaxial film without secondary phases  
 Complete in-plane relaxation (from 8nm)  
 Two crystallographic domains

Stabilization of R-3 phase ( $P_{\text{O}_2} = 2 \times 10^{-7}$  torr)  
 <-> idem  
 <-> idem  
 Four crystallographic domains

# Microstructure and chemical analysis

TEM



(Coll. B. Warot-Fonrose - CEMES)

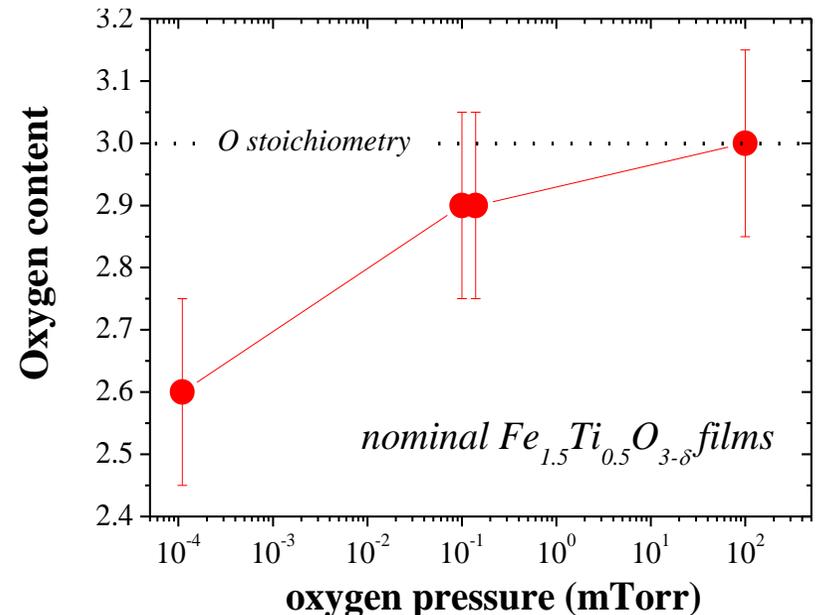
Columnar growth, lateral column size corresponds to the surface grain size measured by AFM (8 nm)

AFM: rms roughness < 1 nm,  
no outgrowths  
"good" for heterostructures

## Chemical analysis by EELS:

- no film/substrate interdiffusion evidenced
- Homogeneity in depth

## RBS+NRA: (Coll. J. Siejka - INSP)



10<sup>-1</sup> Torr : stoichiometric  $\delta=0$   
10<sup>-7</sup> Torr :  $\delta=0.35$

# $\text{Fe}_{1.5}\text{Ti}_{0.5}\text{O}_{3-\delta}$ : control of magnetic properties

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*$\text{Fe}^{2+}$  and  $\text{Fe}^{3+}$ : magnetic*

*$\text{Ti}^{4+}$  is non magnetic*

*Strong importance of Ti/Fe atomic order along  $c_h$  axis : ordered R-3 phase and disordered R-3c*

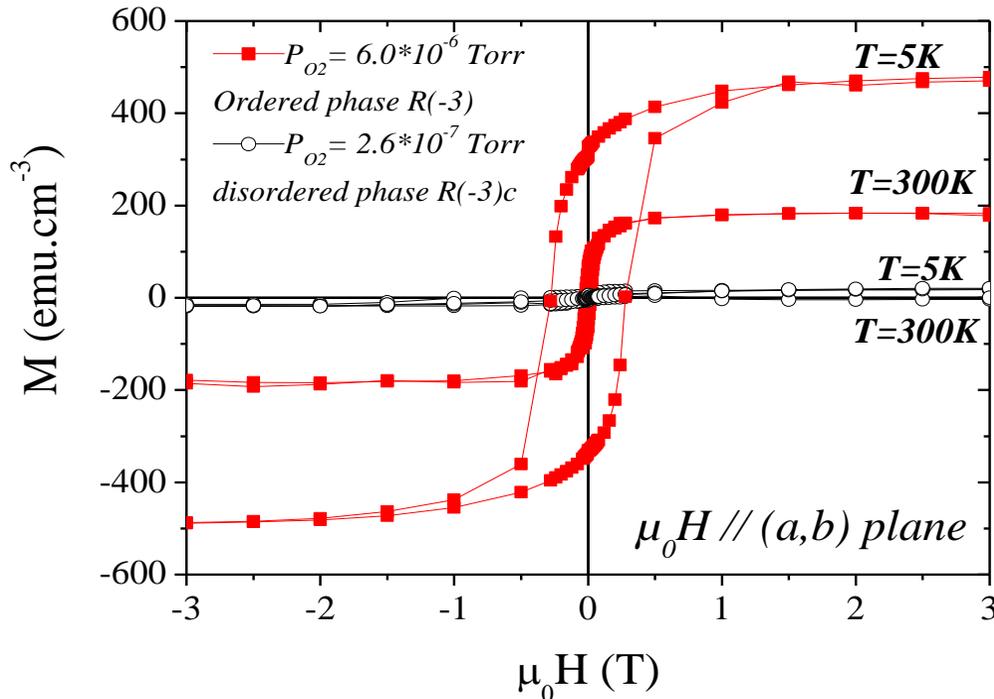
*=> Special routes for growth (bulk and thin films)*

## Our work:

- on  $\text{Al}_2\text{O}_3(0001)$  possibility to form R-3 with  $P_{\text{O}_2} < 10^{-6}$  Torr + annealing but also an hidden parameter (H. Ndilimabaka PhD thesis 2008)
- on  $\text{SrTiO}_3(001)$  stabilizing the R-3 phase with  $P_{\text{O}_2} < 10^{-6}$  Torr + annealing (A. Hamie PhD thesis 2011)

# $Fe_{1.5}Ti_{0.5}O_{3-\delta}$ on $SrTiO_3(001)$

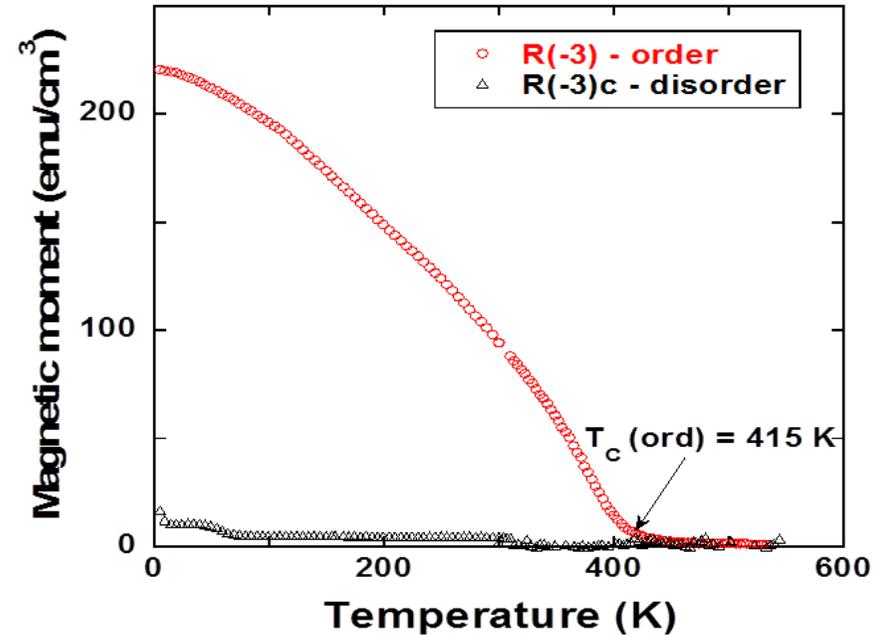
## Comparison R-3 and R-3c phases



A. Hamie et al., *J. Appl. Phys.* 108 (2010) 093710

- $T_c > 400K$
- $M_{Smax} \sim 1.6 \mu_B$ /formula for R-3 (state of the art in bulk)
- $M_{Smax} \sim 0.05 \mu_B$ /formula for R-3c

## From High T VSM:

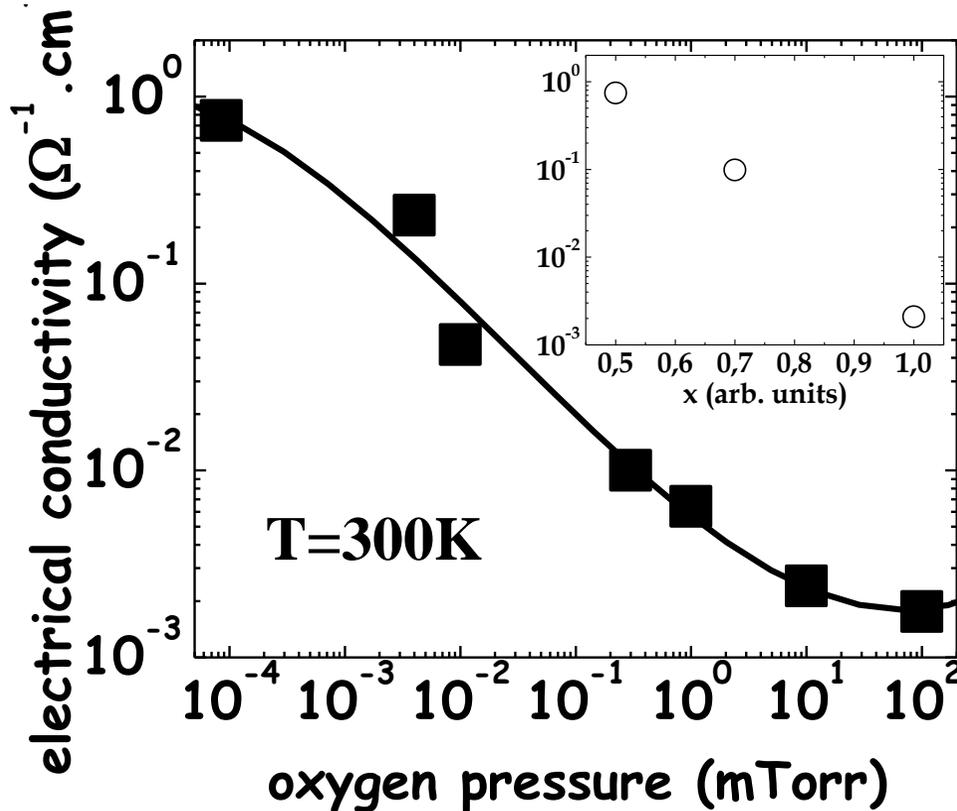


A. Hamie et al., *Appl. Phys. Lett.* 98 (2011) 232501

Y. Ishikawa, *Jpn. J. Phys. Soc.* 13, 37 (1958), 17, 12 (1962)

# $Fe_{1.5}Ti_{0.5}O_{3-\delta}$ : semiconducting properties

**Strong importance of the oxygen stoichiometry on RT electrical conductivity**



With increase of  $\delta$  (decrease of  $P_{O_2}$ ):

- increase of electrical conductivity up to  $1 \Omega^{-1} \text{cm}^{-1}$
- n-type conduction:  $1.21 \times 10^{16} < n < 1.32 \times 10^{18} \text{cm}^{-3}$
- Hall mobility:  $1 < \mu < 8 \text{cm}^2 \text{V}^{-1} \text{s}^{-1}$

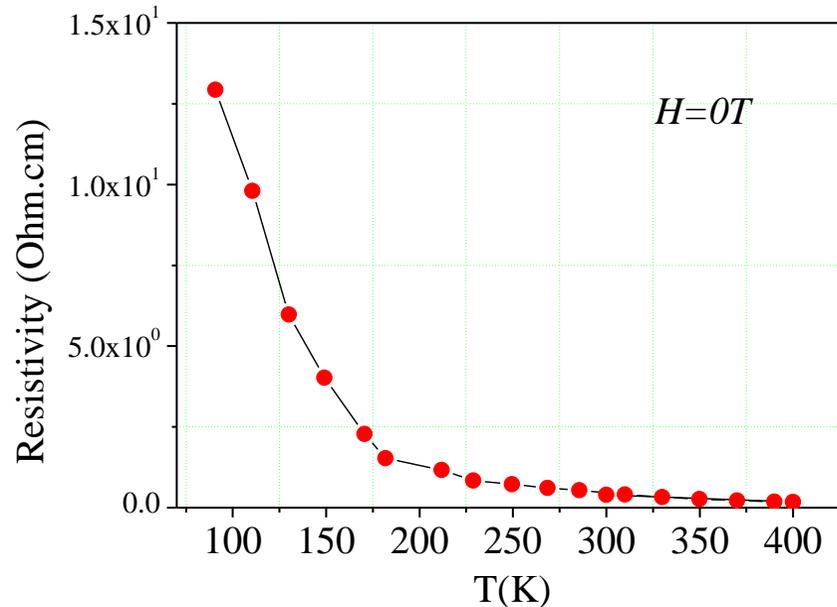
*H. Ndilimabaka et al., J. Appl. Phys. 103, 07D137 (2008),*

*H. Ndilimabaka, PhD thesis Versailles Univ. 5 dec. 2008*

*H. Hojo, et al, Appl. Phys. Lett. 89 (2006) 082509*

# $Fe_{1.5}Ti_{0.5}O_{3-\delta}$ : semiconducting properties

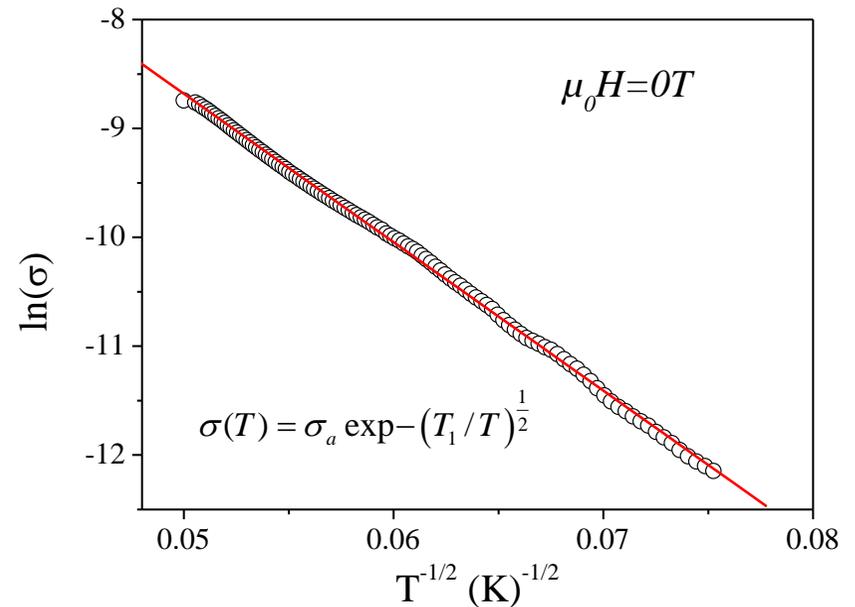
Resistivity versus  $T$  at  $H=0$



*s/c*  $Fe_1Ti_1O_3$  Z.Dai et al., JAP 85,7433, (1999)  
*s/c*  $Fe_{2-x}Ti_xO_3$   $x=0.02;0.06;0.08$  Z.Wang et al.,APL 83,518,(2003)

⇒ Semiconducting behaviour  
 ⇒ Independent of the substrate and of the R-3 or R-3c phases

nature of conductivity:  
 localized carriers



Soft gap Efros-Shklovskii type variable range hopping (ES-VRH)

$$\sigma(T) = \sigma_a \exp\left(-\left(T_1/T\right)^{1/2}\right)$$

B.I. Shklovskii, A.L. Efros, "Electronic properties of doped semiconductors, Springer, Berlin (1984)

# Fe<sub>1.5</sub>Ti<sub>0.5</sub>O<sub>3-δ</sub>: spin polarization

## Magneto-transport H//

Same soft gap VRH type behaviour:

$$\frac{\sigma(H)}{\sigma(0)} = \exp - 2 \left( \frac{C}{k_B T} \right)^{\frac{1}{2}}$$

J. Inoue, S. Maekawa,  
Phys. Rev. B 53 (1996)  
R11927

Interpreted as spin-dependent tunnelling between Fe<sup>2+</sup> to Fe<sup>3+</sup> ions

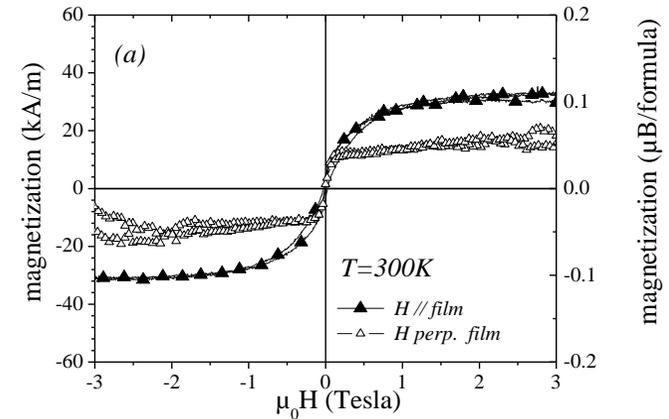
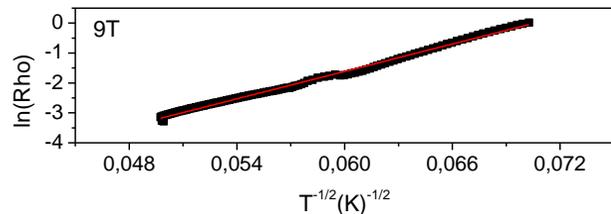
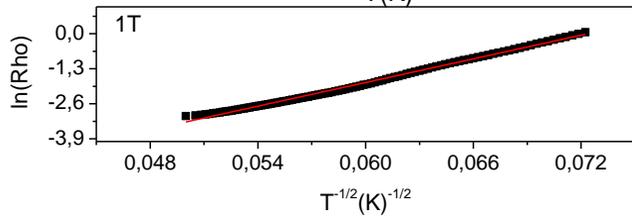
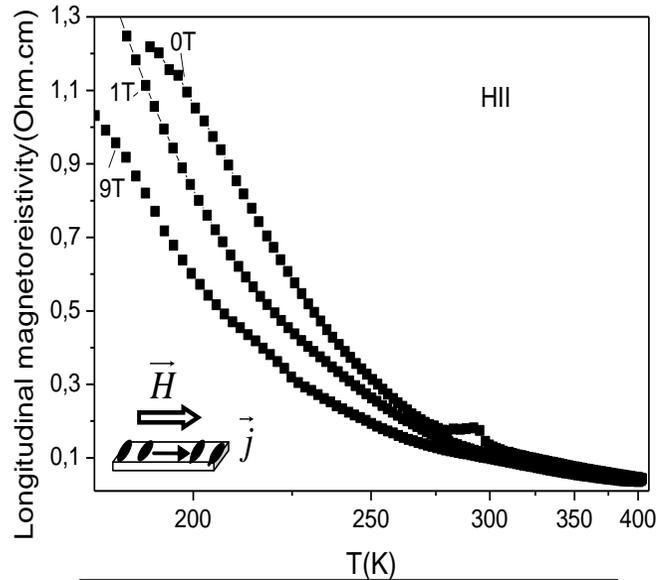
$$MR(H) = \frac{R(H) - R(0)}{R(0)}$$

$$MR_{300K}(1T) = -8\%$$

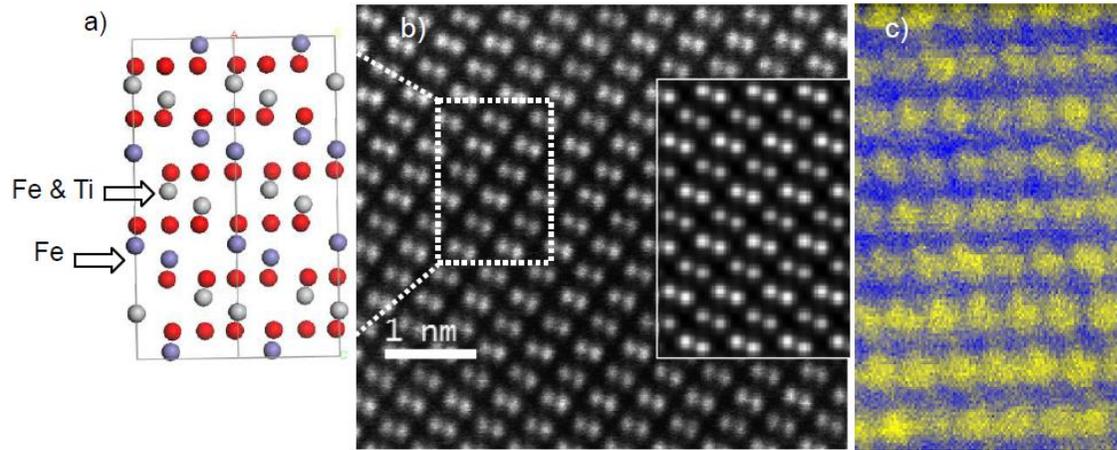
$$MR_{300K}(9T) = -27\%$$

$$\rho(H) = \frac{1}{\sigma(H)} = \frac{\rho(0)}{1 + P^2 m^2} \exp 2 \left( \frac{\kappa C}{k_B T} \right)^{\frac{1}{2}} \quad \text{with } m \equiv \frac{M(H)}{M_{\text{sat}}}$$

$$\Rightarrow \text{in saturation field, } |MR| = \frac{P^2}{1 + P^2} \quad \rightarrow \quad |P| \sim 29\%$$



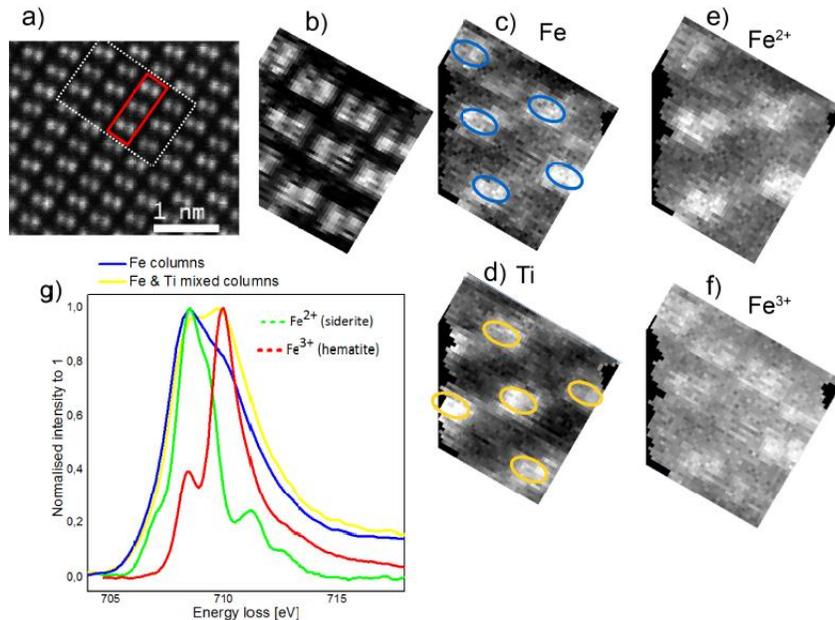
# $Fe_{1.5}Ti_{0.5}O_{3-\delta}$ : evidence of charge order



**Atomic scale resolved STEM and ELNES:**

collab. with L. Bocher, K. March, A. Gloter, O. Stephan (LPS-Orsay)

*Figure 1. a) structural model of  $Fe_{1.5}Ti_{0.5}O_3$ , b) atomically-resolved HAADF image and the simulated image (inset), and c) the corresponding reconstructed false color elemental maps associated with Fe-L<sub>2,3</sub> / Ti-L<sub>2,3</sub> edge intensities (blue/yellow).*



*Figure 2.*

- a) STEM-HAADF image of  $Fe_{1.5}Ti_{0.5}O_{3-d}$*
- b) STEM-HAADF map of the scanned area for EELS acquisition*
- c) and d) Fe-L<sub>2,3</sub> and Ti-L<sub>2,3</sub> elemental maps respectively,*
- e) and f)  $Fe^{2+}$  and  $Fe^{3+}$  reconstructed maps, respectively,*
- g) experimental ELNES Fe-L<sub>3</sub> fine structures extracted from pure Fe (blue) or mixed Fe/Ti (yellow) columns and the corresponding  $Fe^{2+}/Fe^{3+}$  (green/red) ELNES Fe-L<sub>3</sub> edges of reference spectra.*

# $Fe_{1.5}Ti_{0.5}O_{3-\delta}$ : conclusion and perspectives



epitaxial thin films on both  $Al_2O_3(0001)$  and  $SrTiO_3(001)$ :

- A versatile high  $T_c$  magnetic oxide becoming semiconductor
- Magnetism is governed by the atomic Ti/Fe order along c-axis (R-3 vs R-3c)
- Strong influence of oxygen stoichiometry on conductivity
- Hopping conductivity for high  $\delta$
- estimation of polarization from MR in // field : around 29% at room T ...

## Perspectives:

- Understand origin of oxygen deficient conductivity , magnetic anisotropy
- Decorrelate both « R-3 versus R-3c » and «  $\delta$  » parameters in PLD growth
- $FeTiO_3$  in a R3c metastable phase is predicted « multiferroic »...

## Acknowledgments:

**GEMAC - Versailles:**

**PLD and structural:** Elena Popova, Bruno Berini

**Magneto-transport:** Ekaterina Chikoidze

**Magneto-optics:** Niels Keller

**1 PhD on FTO on  $\text{Al}_2\text{O}_3$ :** Hervé Ndilimabaka

**1 PhD on FTO on  $\text{SrTiO}_3$ :** Ali Hamie

**CEMES-Toulouse:** **TEM and EELS:** Benedicte Warot-Fonrose

**LPS-Orsay:** **STEM and ELNES:** L. Bocher, K. March, A. Gloter, O. Stephan

**Tyndall National Institute - Cork:** **Raman** Mircea Modreanu  
**ab-initio calculations** Michael Nolan

**TSU-Tbilisi:** **semiconducting calculations:** Tamar Tchelidze  
**EPR, FMR:** Alexander Shengelaya

**Institute of Physics, PAN-Warsaw:** **PL and ODMR:** Marek Godlewski

**Unité Mixte de Physique CNRS-Thales - Palaiseau:**  
**Nanosized tunnel junctions:** Karim Bouzehouane, Manuel Bibes

**Institut des NanoSciences de Paris - Paris:** **RBS and NRA:** Julius Siejka